

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## NXS0104

Product specification

## Description

This 4-bit non-inverting translator is a bidirectional voltage-level translator and can be used to build digital switching compatibility between multi voltage systems. It uses two separate configurable power supply rails that including A ports supporting operating voltages from 1.65 V to 3.6 V with tracking  $V_{CCA}$  supply, and also including B ports supporting operating voltages from 2.3 V to 5.5 V with tracking  $V_{CCB}$  supply.

The advantage above provides the support of both lower and higher logic signal levels while providing bidirectional translation capabilities between any of the 1.8-V, 2.5-V, 3.3-V, and 5- V voltage circuit points.

Placing output-enable (OE) input to low level, all I/Os are forced to high-impedance state that significantly lower the quiescent current consumption. In order to ensure the high-impedance state during power up or power down, OE pin should be tied to GND via a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

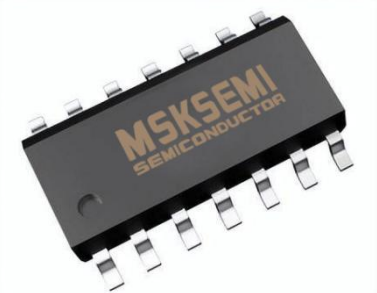
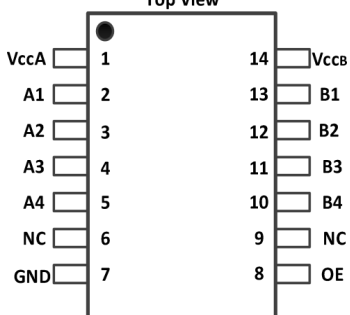
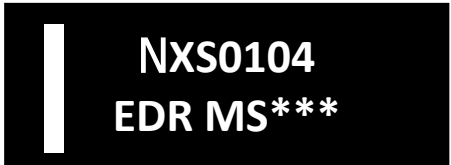
## Features

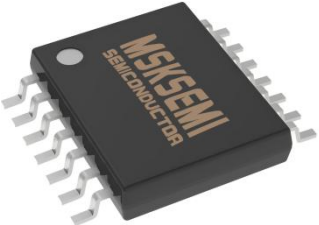
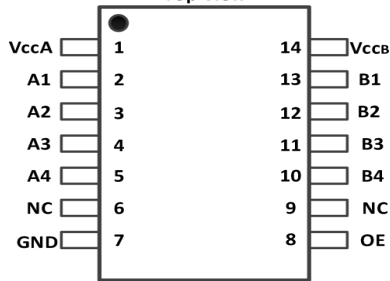

- No direction -control
- Data rates  
24 Mbps (Push Pull)  
2 Mbps (Open)
- 1.65 V to 3.6 V on A port and 2.3 V to 5.5 V on B port ( $V_{CCA} \leq V_{CCB}$ )
- VCC isolation feature: If either VCC input is at GND, both ports are in the high -impedance state
- No power -supply sequencing required: either  $V_{CCA}$  or  $V_{CCB}$  can be ramped first
- $I_{off}$  supports partial -power -down mode operation
- Operating temperature range: -40°C to +85°C


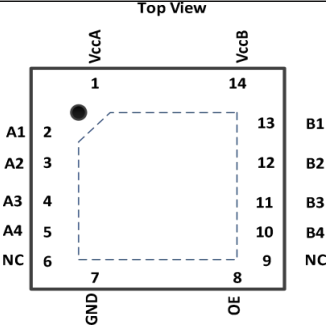

## Applications

- Handset/Smartphone
- MART
- IPC
- GPIO

## Reference News

SOP-14	Pinning and Package	Marking
	<p>Top View</p>  <p>Pin 1: VccA, Pin 2: A1, Pin 3: A2, Pin 4: A3, Pin 5: A4, Pin 6: NC, Pin 7: GND, Pin 8: OE, Pin 9: NC, Pin 10: B4, Pin 11: B3, Pin 12: B2, Pin 13: B1, Pin 14: Vccb</p>	 <p>NXS0104 EDR MS***</p>

TSSOP-14	Pinning and Package	Marking
	<p>Top View</p>  <p>Pin 1: VccA, Pin 2: A1, Pin 3: A2, Pin 4: A3, Pin 5: A4, Pin 6: NC, Pin 7: GND, Pin 8: OE, Pin 9: NC, Pin 10: B4, Pin 11: B3, Pin 12: B2, Pin 13: B1, Pin 14: Vccb</p>	 <p>MSKSEMI 0104PWJ MS***</p>

QFN3.5*3.5-14	Pinning and Package	Marking
	<p>Top View</p> 	

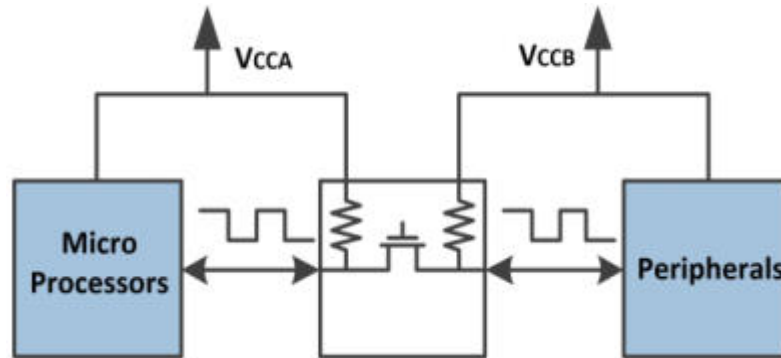
### Device Summary, Pin and Packages (Continued)

Pin				I/O	Function
Name	RGY	D	PW		
V <sub>CCA</sub>	1	1	1	-	Port Supply Voltage. $1.65V \leq V_{CCA} \leq 3.6V$ and $V_{CCA} \leq V_{CCB}$
A1	2	2	2	I/O	Input/Output A1. Referenced to V <sub>CCA</sub> .
A2	3	3	3	I/O	Input/Output A2. Referenced to V <sub>CCA</sub> .
A3	4	4	4	I/O	Input/Output A3. Referenced to V <sub>CCA</sub> .
A4	5	5	5	I/O	Input/Output A4. Referenced to V <sub>CCA</sub> .
NC	6	6	6	-	No internal connection
GND	7	7	7	-	Ground
OE	8	8	8	I	Output Enable(Active High). Pull OE low to place all outputs in 3-state mode. Referenced to V <sub>CCA</sub> .
NC	9	9	9	-	No internal connection
B4	10	10	10	I/O	Input/Output B4. Referenced to V <sub>CCB</sub> .
B3	11	11	11	I/O	Input/Output B3. Referenced to V <sub>CCB</sub> .
B2	12	12	12	I/O	Input/Output B2. Referenced to V <sub>CCB</sub> .
B1	13	13	13	I/O	Input/Output B1. Referenced to V <sub>CCB</sub> .
V <sub>CCB</sub>	14	14	14	-	B Port Supply Voltage. $2.3V \leq V_{CCB} \leq 5.5V$

### Order information

Orderable Device	Package	Packing Option
NXS0104EDR-MS	SOP-14	2500PCS
NXS0104PWJ-MS	TSSOP-14	2000PCS
NXS0104ERGYR-MS	QFN3.5*3.5-14	3000PCS

## Circuit Diagram



## Absolute Maximum Ratings

Parameters		Min	Max	Unit
Supply voltage, $V_{CCA}$		-0.3	6.0	V
Supply voltage, $V_{CCB}$		-0.3	6.0	V
Input voltage range, $V_i$	A port	-0.3	6.0	V
	B port	-0.3	6.0	
Voltage range applied to any output in the high-impedance or power-off state, $V_o$	A port	-0.3	6.0	V
	B port	-0.3	6.0	
Voltage range applied to any output in the high or low state, $V_o$	A port	-0.3	$V_{CCA}+0.3$	V
	B port	-0.3	$V_{CCA}+0.3$	
Input clamp current, $I_{IK}$	$V_i < 0$		-50	mA
Output clamp current, $I_{OK}$	$V_o < 0$		-50	mA
Continuous output current, $I_o$			$\pm 50$	mA
Continuous current through $V_{CCA}$ , $V_{CCB}$ or GND			$\pm 100$	mA
Maximum junction temperature			150	$^{\circ}\text{C}$
Storage temperature range		-65	150	$^{\circ}\text{C}$

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The value of  $V_{CCA}$  and  $V_{CCB}$  are provided in the recommended operating conditions table.

## ESD Ratings

ESD			Value	Unit
V(ESD)	Electrostatic Discharge	Human-Body Model (HBM) <sup>(1)</sup>	$\pm 3\text{K}$	V
		Charged-Device Model (CDM) <sup>(2)</sup>	$\pm 2\text{K}$	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## Recommended Operating Conditions

$V_{CCI}$  is the supply voltage associated with the input port.  $V_{CCO}$  is the supply Voltage associated with the output port.

Parameter	Conditions		Min	Typ	Max	Unit
Supply voltage <sup>(1)</sup>	$V_{CCA}$		1.65		3.6	V
	$V_{CCB}$		2.3		5.5	
High-level input voltage ( $V_{IH}$ )	A-port I/Os	$V_{CCA}=1.65\text{ V to }1.95\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	$V_{CCI}-0.2$		$V_{CCI}$	V
		$V_{CCA}=2.3\text{ V to }3.6\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	$V_{CCI}-0.4$		$V_{CCI}$	
	B-port I/Os	$V_{CCA}=1.65\text{ V to }3.6\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	$V_{CCI}-0.4$		$V_{CCI}$	
	OE input	$V_{CCA}=1.65\text{ V to }3.6\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	$V_{CCI} \times 0.8$		5.5	
Low-level input voltage ( $V_{IL}$ ) <sup>(2)</sup>	A-port I/Os	$V_{CCA}=1.65\text{ V to }1.95\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	0		0.15	V
	B-port I/Os	$V_{CCA}=1.65\text{ V to }3.6\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	0		0.15	
OE	OE input	$V_{CCA}=1.65\text{ V to }3.6\text{ V}$ $V_{CCB}=2.3\text{ V to }5.5\text{ V}$	0		$V_{CCA} \times 0.25$	V
Input transition rise or fall rate ( $\Delta t/\Delta v$ )	A-port I/Os push-pull driving				10	ns/V
	B-port I/Os push-pull driving				10	
	Control input				10	
TA Operating free- air temperature	-		-40		85	°C

(1)  $V_{CCA}$  must be less than or equal to  $V_{CCB}$ .

(2) The maximum  $V_{IL}$  value is provided to ensure that a valid  $V_{OL}$  is maintained. The  $V_{OL}$  value is  $V_{IL}$  plus the voltage drop across the pass gate transistor.

## Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted) <sup>(1) (2) (3)</sup>

Parameter		Conditions	V <sub>CCA</sub>	V <sub>CCB</sub>	Temp	Min	Typ	Max	Unit
V <sub>OHA</sub>	PortA Output High Voltage	I <sub>OH</sub> =−20 μA V <sub>IB</sub> ≥ V <sub>CCB</sub> − 0.4V	1.65V to 3.6V	2.3V to 5.5V	Full	V <sub>CCA</sub> ×0.7			V
V <sub>OLA</sub>	PortA Output Low Voltage	I <sub>OL</sub> =1mA V <sub>IB</sub> ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V
V <sub>OHB</sub>	PortB Output High Voltage	I <sub>OH</sub> =−20 μA V <sub>IA</sub> ≥ V <sub>CCA</sub> − 0.4V	1.65V to 3.6V	2.3V to 5.5V	Full	V <sub>CCA</sub> ×0.7			V
V <sub>OLB</sub>	PortB Output Low Voltage	I <sub>OL</sub> =1mA V <sub>IA</sub> ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V
I <sub>I</sub>	Input Leakage Current	OE	1.65V to 3.6V	2.3V to 5.5V	+25°C			±1	μA
					Full			±1.5	
I <sub>off</sub>	Partial Power Down Current	A Ports	0V	0V to 5.5V	+25°C			±0.5	μA
					Full			±1	
		B Ports	0V to 3.6V	0V	+25°C			±0.5	
					Full			±1	
I <sub>OZ</sub>	High-impedance State Output Current	A or B port OE=0V	1.65V to 3.6V	2.3V to 5.5V	+25°C			±0.5	μA
					Full			±1	
I <sub>CCA</sub>	V <sub>CCA</sub> Supply Current	V <sub>I</sub> =V <sub>O</sub> =open I <sub>O</sub> =0	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			2.5	μA
			3.6v	0V	Full			2.5	
			0v	5.5V	Full			-1	
I <sub>CCB</sub>	V <sub>CCB</sub> Supply Current	V <sub>I</sub> =V <sub>O</sub> =open I <sub>O</sub> =0	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			10	μA
			3.6v	0V	Full			-1	
			0v	5.5V	Full			1	
I <sub>CCA</sub> + I <sub>CCB</sub>	Combined Supply Current	V <sub>I</sub> =V <sub>CC1</sub> or GND I <sub>O</sub> =0	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			13	μA
I <sub>CCA</sub>	V <sub>CCA</sub> Supply Current	V <sub>I</sub> =V <sub>CC1</sub> or 0V I <sub>O</sub> =0, OE=0V	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			1	μA
I <sub>CCB</sub>	V <sub>CCB</sub> Supply Current	V <sub>I</sub> =V <sub>CC1</sub> or 0V I <sub>O</sub> =0, OE=0V	2.3v to 3.6V	2.3v to 5.5V	Full			1	μA
C <sub>i</sub>	Input Capacitance	OE	3.3V	3.3V	+25°C		2.5		PF
C <sub>io</sub>	Input-to-output Internal Capacitance	A Port	3.3V	3.3V	+25°C		5		PF
		B Port	3.3V	3.3V	+25°C		5		

(1) V<sub>CC1</sub> is the VCC associated with the input port.

(2) V<sub>CC0</sub> is the VCC associated with the output port

(3) V<sub>CCA</sub> must be less than or equal to V<sub>CCB</sub>.

## Timing Requirements

**$V_{CCA}=1.8V\pm0.15V$**

		<b><math>V_{CCB}=2.5V\pm0.2V</math></b>	<b><math>V_{CCB}=3.3V\pm0.2V</math></b>	<b><math>V_{CCB}=5V\pm0.2V</math></b>	<b>Unit</b>
		<b>Typ</b>	<b>Typ</b>	<b>Typ</b>	
Data Rate	Push-pull Driving	21	22	24	Mbps
	Open-drain Driving	2	2	2	
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	47	45	41	ns
	Open-drain Driving (Data Inputs)	500	500	500	

**$V_{CCA}=2.5V\pm0.15V$**

		<b><math>V_{CCB}=2.5V\pm0.2V</math></b>	<b><math>V_{CCB}=3.3V\pm0.2V</math></b>	<b><math>V_{CCB}=5V\pm0.2V</math></b>	<b>Unit</b>
		<b>Typ</b>	<b>Typ</b>	<b>Typ</b>	
Data Rate	Push-pull Driving	20	22	24	Mbps
	Open-drain Driving	2	2	2	
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	50	45	41	ns
	Open-drain Driving (Data Inputs)	500	500	500	

**$V_{CCA}=3.3V\pm0.15V$**

		<b><math>V_{CCB}=3.3V\pm0.2V</math></b>	<b><math>V_{CCB}=5V\pm0.2V</math></b>	<b>Unit</b>
		<b>Typ</b>	<b>Typ</b>	
Data Rate	Push-pull Driving	23	24	Mbps
	Open-drain Driving	2	2	
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	43	41	ns
	Open-drain Driving (Data Inputs)	500	500	

## Switching Characteristics: $V_{CC}=1.8V \pm 0.15V$

over recommended operating free-air temperature range (unless otherwise noted)

Parameter		Conditions		$V_{CCB}=2.5V \pm 0.2V$	$V_{CCB}=3.3V \pm 0.2V$	$V_{CCB}=5V \pm 0.2V$	Units
				Typ	Typ	Typ	
$t_{PHL}$	Propagation Delay Time High-to-low Output	A to B	Push-pull Driving	5.6	5	5	ns
			Open-drain Driving	7.5	7.9	8.3	
$t_{PLH}$	Propagation Delay Time low-to-high Output	A to B	Push-pull Driving	10.0	9.5	9	ns
			Open-drain Driving	181	170	154	
$t_{PHL}$	Propagation Delay Time High-to-low Output	B to A	Push-pull Driving	7	7.1	7.2	ns
			Open-drain Driving	7.6	8.1	9.2	
$t_{PLH}$	Propagation Delay Time low-to-high Output	B to A	Push-pull Driving	7.6	6.9	6	ns
			Open-drain Driving	163	145	118	
$t_{en}$	Enable Time	OE to A or B		135	159	182	ns
$t_{dis}$	Disable Time	OE to A or B		170	174	181	ns
$t_{rA}$	Input Rise Time	A port rise time	Push-pull Driving	13.4	11.9	10.6	ns
			Open-drain Driving	68	66	62	
$t_{rB}$	Input Rise Time	B port rise time	Push-pull Driving	13	12	11.6	ns
			Open-drain Driving	66	65	50	
$t_{fA}$	Input Fall Time	A port fall time	Push-pull Driving	5.6	4.7	4.0	ns
			Open-drain Driving	5.0	5.1	5.2	
$t_{fB}$	Input Fall Time	B port fall time	Push-pull Driving	3.0	3.0	2.9	ns
			Open-drain Driving	6.1	5.6	4.4	
$t_{SK(O)}$	Skew(time), Output	Channel-to-Channel Skew		0.5	0.5	0.5	ns
Maximum Data Rate		Push-pull Driving		22	23	24	Mbps
		Open-drain Driving		2	2	2	



## Switching Characteristics: $V_{CC}=2.5V \pm 0.15V$

over operating free-air temperature range (unless otherwise noted)

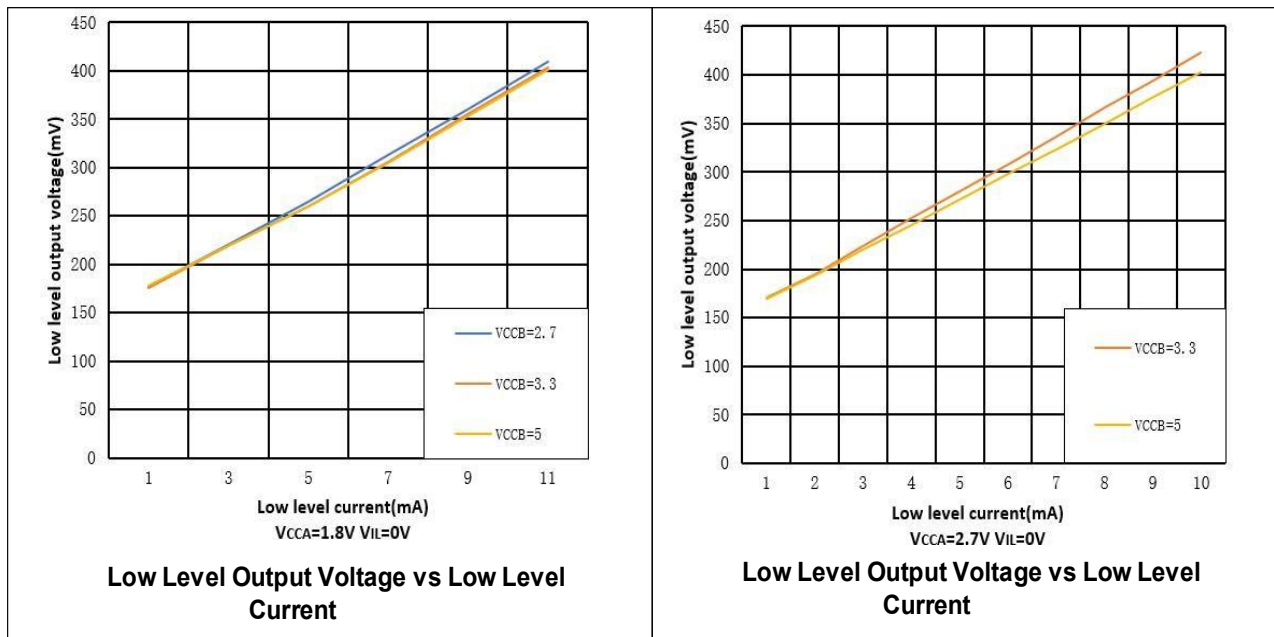
Parameter		Conditions		$V_{CCB}=2.5V \pm 0.2V$	$V_{CCB}=3.3V \pm 0.2V$	$V_{CCB}=5V \pm 0.2V$	Units
				Typ	Typ	Typ	
$t_{PHL}$	Propagation Delay Time High-to-low Output	A to B	Push-pull Driving	3.5	3.5	3.2	ns
			Open-drain Driving	6.3	6.5	6.7	
$t_{PLH}$	Propagation Delay Time low-to-high Output	A to B	Push-pull Driving	4.5	4.9	4.7	ns
			Open-drain Driving	158	152	142	
$t_{PHL}$	Propagation Delay Time High-to-low Output	B to A	Push-pull Driving	3.7	3.9	4.6	ns
			Open-drain Driving	6	6.6	7.7	
$t_{PLH}$	Propagation Delay Time low-to-high Output	B to A	Push-pull Driving	4.8	4	2.5	ns
			Open-drain Driving	153	138	116	
$t_{en}$	Enable Time	OE to A or B		7.7	41.8	130	ns
$t_{dis}$	Disable Time	OE to A or B		175	181	182	ns
$t_{rA}$	Input Rise Time	A port Rise Time	Push-pull Driving	9.8	8.6	7.5	ns
			Open-drain Driving	79	77	65	
$t_{rB}$	Input Rise Time	B port Rise Time	Push-pull Driving	9.8	8.7	8.1	ns
			Open-drain Driving	93	68	53	
$t_{fA}$	Input Fall Time	Aport Fall Time	Push-pull Driving	4.6	4.1	3.6	ns
			Open-drain Driving	5.1	5.1	5.2	
$t_{fB}$	Input Fall Time	Bport Fall Time	Push-pull Driving	4.5	4.0	4.0	ns
			Open-drain Driving	6.9	7.4	7.8	
$t_{SK(O)}$	Skew(time), Output	Channel-to-Channel Skew		0.5	0.5	0.5	ns
Maximum Data Rate		Push-pull Driving		22	24	24	Mbps
		Open-drain Driving		2	2	2	

## Switching Characteristics: $V_{CC}=3.3V\pm0.15V$

over recommended operating free-air temperature range (unless otherwise noted)

Parameter		Conditions		$V_{CCB}=3.3V\pm0.2V$	$V_{CCB}=5V\pm0.2V$	Units
				TYP	TYP	
$t_{PHL}$	Propagation Delay Time High-to-low Output	A to B	Push-pull Driving	2.1	2.2	ns
			Open-drain Driving	5.9	6.1	
$t_{PLH}$	Propagation Delay Time High-to-low Output	A to B	Push-pull Driving	1	3.3	ns
			Open-drain Driving	138	131	
$t_{PHL}$	Propagation Delay Time High-to-low Output	B to A	Push-pull Driving	2.3	2.6	ns
			Open-drain Driving	5.4	6.6	
$t_{PLH}$	Propagation delay time low-to-high Output	B to A	Push-pull Driving	1.0	1.0	ns
			Open-drain Driving	133	115	
$t_{en}$	Enable Time	OE to A or B		4.7	5.2	ns
$t_{dis}$	Disable Time	OE to A or B		174	182	ns
$t_{rA}$	Input Rise Time	A port Rise Time	Push-pull Driving	7.4	6.6	ns
			Open-drain Driving	75	67	
$t_{rB}$	Input Rise Time	B port Rise Time	Push-pull Driving	7.7	7.1	ns
			Open-drain Driving	70	65	
$t_{fA}$	Input Fall Time	Aport Fall Time	Push-pull Driving	3.4	3.0	ns
			Open-drain Driving	5.1	5.1	
$t_{fB}$	Input Fall Time	Bport Fall Time	Push-pull Driving	3.5	3.2	ns
			Open-drain Driving	6.8	6.7	
$t_{sk(o)}$	Skew(time), Output	Channel-to-Channel Skew		0.5	0.5	ns
Maximum Data Rate		Push-pull Driving		24	24	Mbps
		Open-drain Driving		2	2	

## Typical Characteristics

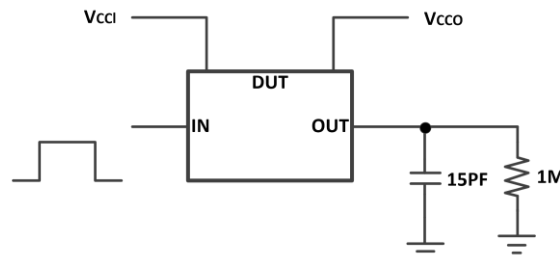


## Parameter Measurement Information

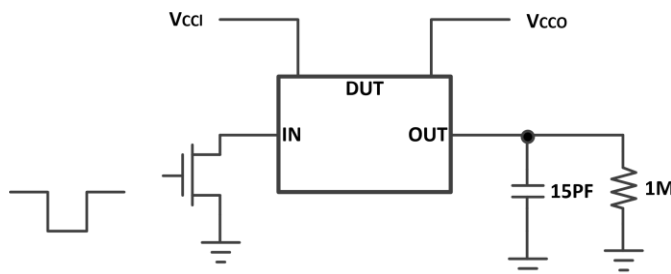
Unless otherwise noted, all input pulsed are supplied by generators having the following characteristics:

- PSRR 10MHz
- $Z_o=50\ \Omega$
- $dv/dt \geq 1V/ns$

Note: All input pulses are measured one at a time with one transition per measurement

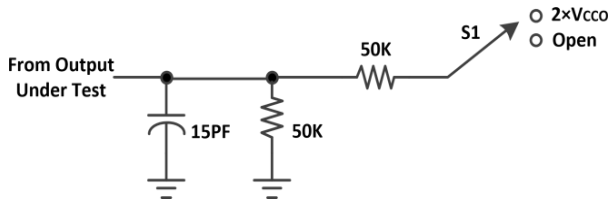


**Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using a Push-Pull Driver**



**Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using an Open-Drain Driver**

# Parameter Measurement Information (Continued)

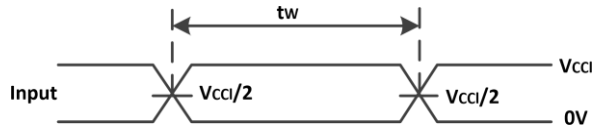


**Load Circuit for Enable/Disable Time Measurement**

**Switch Configuration for Enable/Disable Timing**

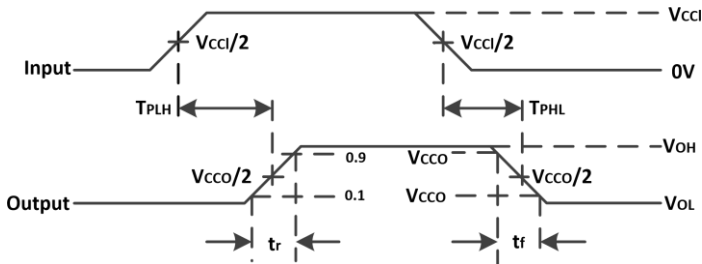
Test	S1
$t_{PZL}^{(1)}$ , $t_{PLZ}^{(2)}$	$2 \times V_{CCO}$
$t_{PHZL}^{(1)}$ , $t_{PZH}^{(2)}$	Open

- (1)  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .  
 (2)  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .

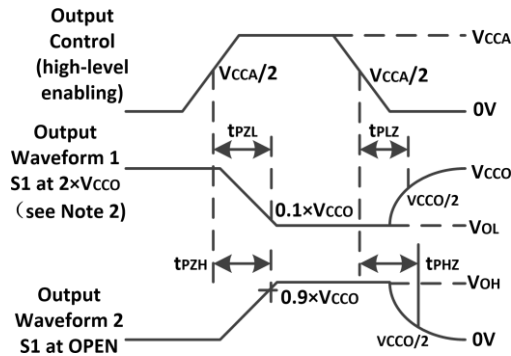


- (1) All input pulses are measured one at a time, with one transition per measurement.

**Voltage Waveforms Pulse Duration**



**Voltage Waveforms Propagation Delay Times**



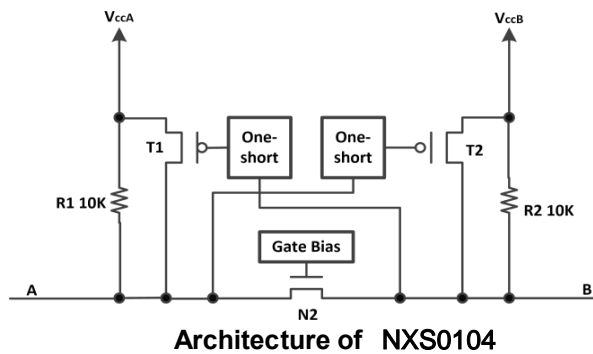
**Voltage Waveforms Enable and Disable**

## Overview

The NXS0104 IC is a Bi-direction voltage-level translator specifically designed for translating logic voltage levels. The A port can accept I/O voltages that cover from 1.65 V to 3.6 V range; The B port can accept I/O voltages from 2.3 V to 5.5 V. The device is a pass-gate architecture with edge-rate accelerators (one-shots) to improve the overall data rate. 10-k $\Omega$  pullup resistors that usually used in open-drain applications have been integrated inside IC with the advantage saving an external resistor. Not only the IC is designed for open-drain applications, but also this device can translate push-pull CMOS logic outputs.

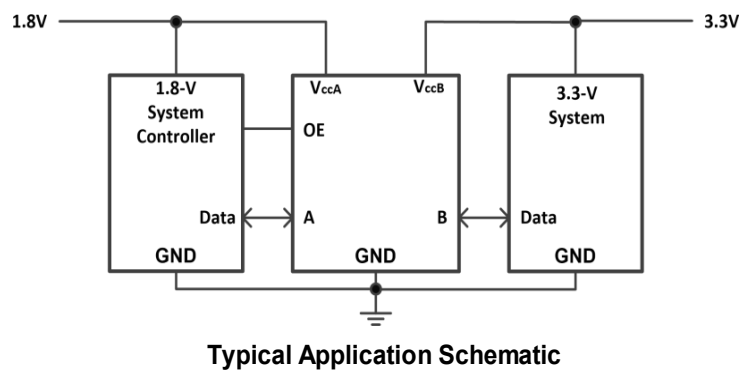
## Architecture

The NXS0104 architecture (see Figure below) is a translator with Bi-direction-Sensing function that means a direction-control mechanism to control the direction of data flow from A to B or from B to A is not needed. These two bidirectional channels independently determine the direction of data flow without a direction-control signal. This auto-direction feature is realized by each I/O pin can be automatically reconfigured as either an input or an output.



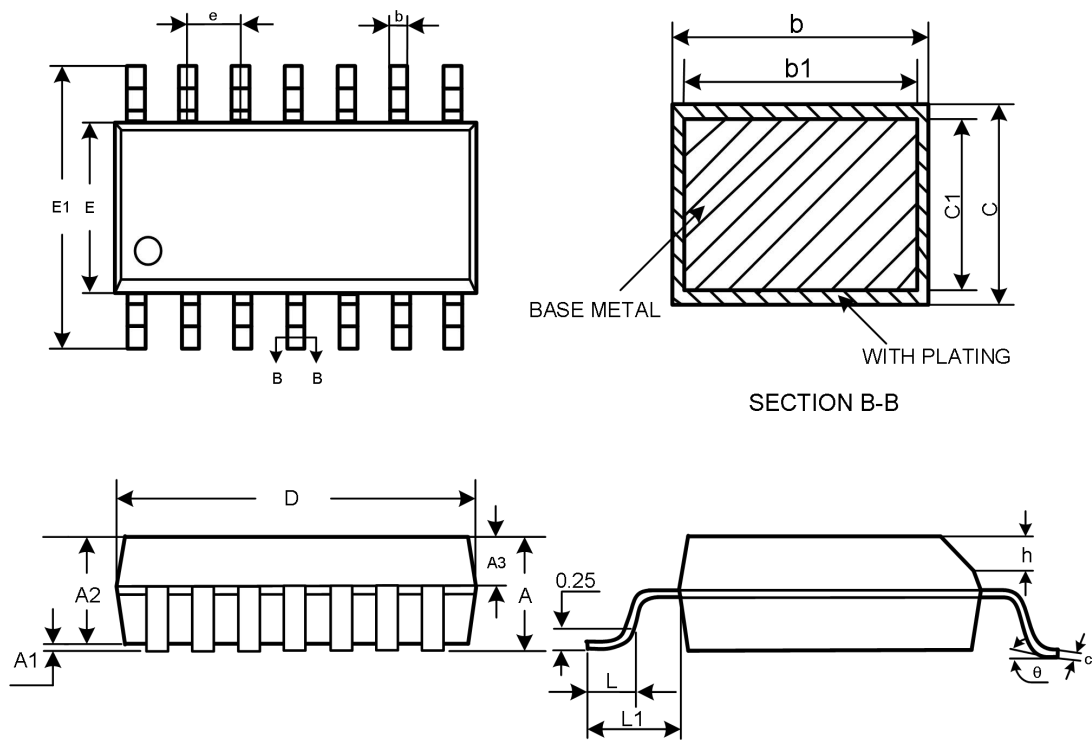
## Application Information

The NXS0104 device can be used to bridge the digital-switching compatibility gap between two voltage nodes to successfully interface logic threshold levels found in electronic systems. It should be used in a point-to-point topology for interfacing devices or systems operating at different interface voltages with one another. Its primary target application use is for interfacing with open-drain drivers on the data I/Os such as I2C or 1-wire, where the data is bidirectional and no control signal is available. The device can also be used in applications where a push-pull driver is connected to the data I/Os, but the NXS0104 might be a better option for such push-pull applications.



Package Outline Dimension

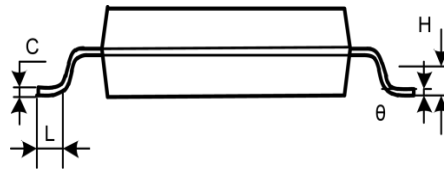
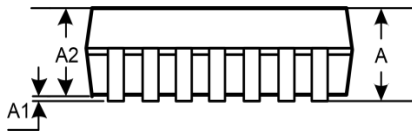
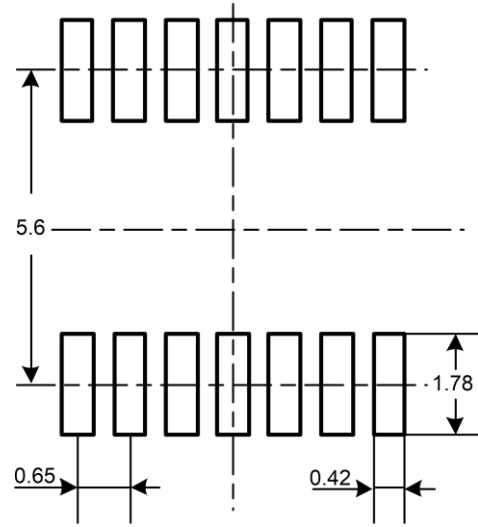
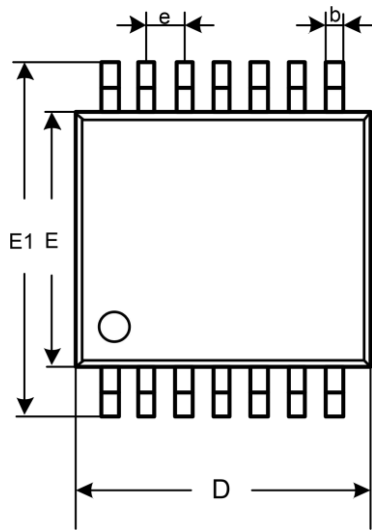
SOP-14



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min	Nom	Max	Min	Nom	Max
A	—	—	1.750	—	—	0.069
A1	0.100	—	0.225	0.004	—	0.009
A2	1.300	1.400	1.500	0.051	0.055	0.059
A3	0.600	0.650	0.700	0.024	0.026	0.028
b	0.390	—	0.470	0.015	—	0.019
b1	0.380	0.410	0.440	0.015	0.016	0.017
c	0.200	—	0.240	0.008	—	0.009
c1	0.190	0.200	0.210	0.007	0.008	0.008
D	8.550	8.650	8.750	0.337	0.341	0.344
E	5.800	6.000	6.200	0.228	0.236	0.244
E1	3.800	3.900	4.000	0.150	0.154	0.157
e	0.250	1.270BSC	0.500	0.010	0.05BSC	0.020
h	0.500	—	0.800	0.020	—	0.031
L	—	—	—	—	—	—
L1	—	1.050REF	—	—	0.041REF	—
θ	0°	—	8°	0°	—	8°

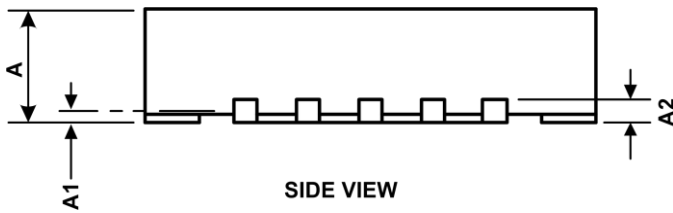
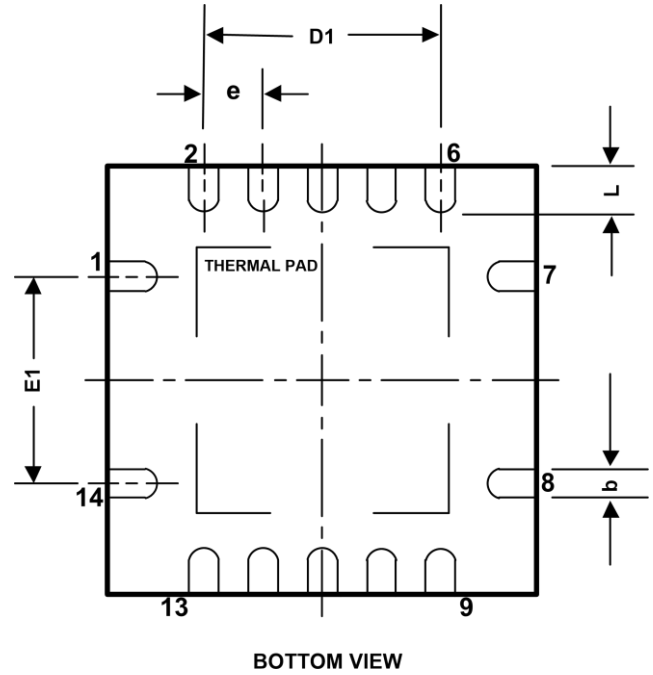
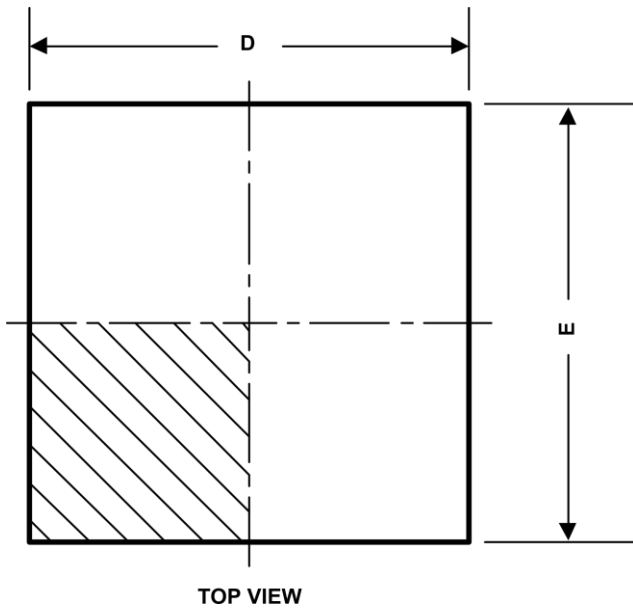
## Package Outline Dimension

### TSSOP-14



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Min
A		1.200		0.047
A1	0.050	0.150	0.002	0.006
A2	0.800	1.050	0.031	0.041
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
D	4.860	5.100	0.191	0.201
E	4.300	4.500	0.169	0.177
E1	6.250	6.550	0.246	0.258
e	0.650BSC		0.026BSC	
L	0.500	0.700	0.020	0.028
H	0.250TYP		0.010TYP	
$\theta$	1°	7°	1°	7°

**Package Outline Dimension**  
**QFN3.5\*3.5-14**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.000	0.031	0.039
A1	0.000	0.050	0.00	0.002
A2	0.200REF		0.008REF	
b	0.180	0.300	0.007	0.012
D	3.350	3.650	0.132	0.144
D1	2.000TYP		0.079TYP	
E	3.350	3.650	0.007	0.012
E1	1.500TYP		0.059TYP	
e	0.500TYP		0.020TYP	
L	0.300	0.500	0.012	0.020



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